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## Patent Abstracts of Japan

PUBLICATION NUMBER : 06291039  
PUBLICATION DATE : 18-10-94

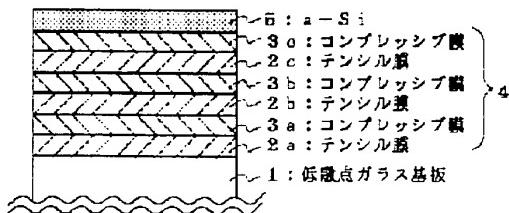
APPLICATION DATE : 06-04-93  
APPLICATION NUMBER : 05105003

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INT.CL. : H01L 21/20 H01L 21/268 H01L 21/314  
H01L 29/784 H01L 21/336

TITLE : AMORPHOUS-SEMICONDUCTOR  
FORMATION SUBSTRATE AND  
MANUFACTURE OF  
POLYCRYSTALLINE-SEMICONDUCTOR  
FORMATION SUBSTRATE USING IT



ABSTRACT : PURPOSE: To provide an amorphous semiconductor formation substrate whose film thickness is comparatively thick so as not to thermally damage a low-melting-point glass substrate and which is provided with a buffer layer not increasing an internal stress due to the thick film thickness.

CONSTITUTION: An amorphous semiconductor formation substrate is formed in such a way that an a-Si film 5 is formed on a low-melting-point glass substrate 1 via a buffer layer 4 for impurity-diffusion prevention. In the formation substrate, the buffer layer 4 is formed of a film in which tensile films 2a to 2c composed of SiO<sub>2</sub> and compressive films 3a to 3c composed of SiO<sub>2</sub> in the same manner have been laminated alternately.

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